

RJL6012DPE

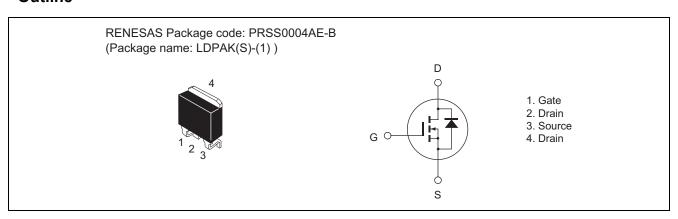
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1750-0100 Rev.1.00 Oct 26, 2009

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|---------------------------------------------|-------------------------------|-------------|------|
| Drain to Source voltage | V_{DSS} | 600 | V |
| Gate to Source voltage | V_{GSS} | ±30 | V |
| Drain current | I _D | 10 | Α |
| Drain peak current | I _{D (pulse)} Note1 | 30 | Α |
| Body-Drain diode reverse Drain current | I _{DR} | 10 | Α |
| Body-Drain diode reverse Drain peak current | I _{DR (pulse)} Note1 | 30 | Α |
| Avalanche current | I _{AP} Note3 | 3 | Α |
| Avalanche energy | E _{AR} Note3 | 0.49 | mJ |
| Channel dissipation | Pch Note2 | 100 | W |
| Channel to case thermal impedance | θch-c | 1.25 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

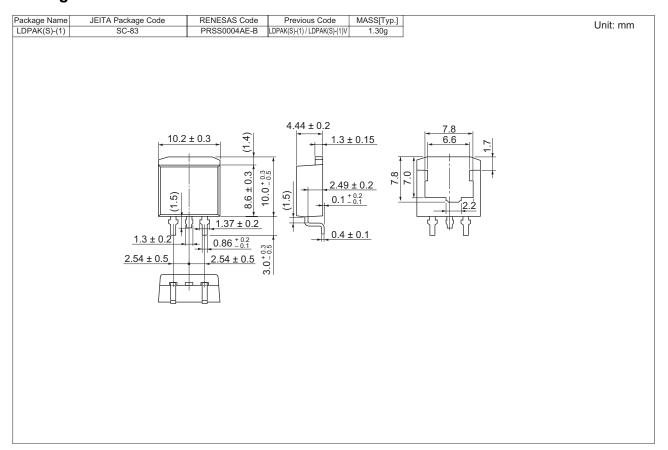
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--------------------------------------------|---------------------|-----|------|------|------|----------------------------------------------------------------------------|
| Drain to Source breakdown voltage | $V_{(BR)DSS}$ | 600 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero Gate voltage drain current | I _{DSS} | _ | _ | 10 | μΑ | $V_{DS} = 600 \text{ V}, V_{GS} = 0$ |
| Gate to Source leak current | I _{GSS} | _ | _ | ±0.1 | μΑ | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$ |
| Gate to Source cutoff voltage | $V_{GS(off)}$ | 2.0 | _ | 4.0 | V | V_{DS} = 10 V, I_{D} = 1 mA |
| Static Drain to Source on state resistance | R _{DS(on)} | 1 | 0.88 | 1.10 | Ω | $I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$ |
| Input capacitance | Ciss | | 1050 | | pF | V _{DS} = 25 V |
| Output capacitance | Coss | | 105 | | pF | V _{GS} = 0 |
| Reverse transfer capacitance | Crss | | 12 | | pF | f = 1 MHz |
| Turn-on delay time | $t_{d(on)}$ | | 27 | _ | ns | I _D = 5 A |
| Rise time | t _r | _ | 20 | _ | ns | V _{GS} = 10 V |
| Turn-off delay time | $t_{d(off)}$ | _ | 78 | _ | ns | $R_L = 60 \Omega$ |
| Fall time | t _f | _ | 16 | _ | ns | $Rg = 10 \Omega$ |
| Total Gate charge | Qg | _ | 28 | _ | nC | V _{DD} = 480 V |
| Gate to Source charge | Qgs | _ | 4.8 | _ | nC | V _{GS} = 10 V |
| Gate to Drain charge | Qgd | _ | 14.2 | _ | nC | I _D = 10 A |
| Body-Drain diode forward voltage | V_{DF} | _ | 1.0 | 1.7 | V | $I_F = 10 \text{ A}, V_{GS} = 0^{\text{Note4}}$ |
| Body-Drain diode reverse recovery time | trr | _ | 150 | _ | ns | $I_F = 10 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$ |

Notes: 4. Pulse test

Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJL6012DPE-00-J3 | 1000 pcs | Taping |

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